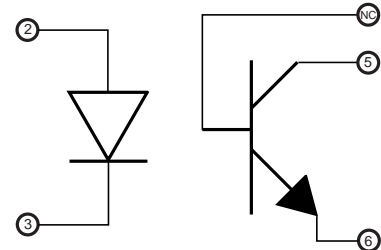




Phototransistor Optocoupler

Features

- 2,500 Volt electrical isolation
- Standard 8-pin DIP package
- High current transfer ratio for low IF
- Screening similar to JANTX, JANTXV or JANS equivalent



Description

- The MXP1158 consists of a light emitting diode and an NPN phototransistor.
- The device is available in a hermetic 8-pin DIP package.

Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	Min	Max	UNITS
IC(on)	On-State Collector Current	IF = 1 mA, VCE = 5 Volts	1.0	8.0	mAmps
VCEsat	Saturation Voltage	IF = 2 mA, IC = 1.0 mA		0.3	Volts
BVceo	Breakdown Voltage	IC = 1.0 mA	40		Volts
BVebo	Breakdown Voltage	Ieb = 100 uA	7		Volts
ICE(off)	Off-State Leakage Current	VC = 20 Volts	100		nAmps
VF	Input Forward Voltage	IF = 10 mA	1.0		Volts
IR	Input Reverse Current	VR = 2.0 V	100.0		uAmps
tR	Rise Time	VCC = 10 Volts, RL = 100 Ohms		20	usec
tF	Fall Time	IF = 5 mA		20	usec

Absolute Maximum Ratings

LED Input Diode

Reverse Voltage	2.0 Vdc minimum @ IR = 10 uA
Forward Voltage	1.95 Vdc maximum @ IF = 100 mA
Peak Forward Current	1.0 Amp @ 1 msec pulse width
Power Dissipation	200 mW
Input to Output Isolation	+/- 2,500 Vdc
Storage Temperature Range	-65 C to +150 C
Operating Temperature Range	-55 C to +125 C

